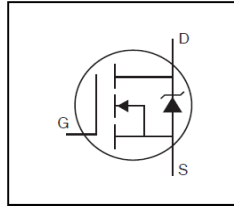


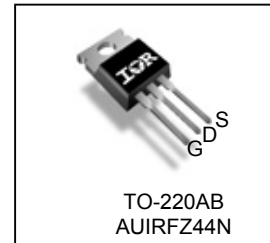
**Features**

- Advanced Planar Technology
- Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified \*



HEXFET® Power MOSFET

<b>V<sub>DSS</sub></b>	<b>55V</b>
<b>R<sub>DS(on)</sub> max.</b>	<b>17.5mΩ</b>
<b>I<sub>D</sub></b>	<b>49A</b>



<b>G</b>	<b>D</b>	<b>S</b>
Gate	Drain	Source

**Description**

Specifically designed for Automotive applications, this Stripe Planar design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRFZ44N	TO-220	Tube	50	AUIRFZ44N

**Absolute Maximum Ratings**

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (TA) is 25°C, unless otherwise specified.

Symbol	Parameter	Max.	Units
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	49	A
I <sub>D</sub> @ T <sub>C</sub> = 100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	35	
I <sub>DM</sub>	Pulsed Drain Current ①	160	
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Power Dissipation	94	W
	Linear Derating Factor	0.63	W/°C
V <sub>GS</sub>	Gate-to-Source Voltage	± 20	V
E <sub>AS</sub>	Single Pulse Avalanche Energy (Thermally Limited) ⑥	150	mJ
E <sub>AS</sub> (Tested)	Single Pulse Avalanche Energy Tested Value ⑤	530	
I <sub>AR</sub>	Avalanche Current ①	25	A
E <sub>AR</sub>	Repetitive Avalanche Energy ①	9.4	mJ
dv/dt	Peak Diode Recovery dv/dt③	5.0	V/ns
T <sub>J</sub>	Operating Junction and Storage Temperature Range	-55 to + 175	°C
T <sub>STG</sub>			
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

**Thermal Resistance**

Symbol	Parameter	Typ.	Max.	Units
R <sub>θJC</sub>	Junction-to-Case	—	1.5	°C/W
R <sub>θCS</sub>	Case-to-Sink, Flat, Greased Surface	0.50	—	
R <sub>θJA</sub>	Junction-to-Ambient	—	62	

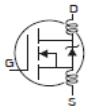
HEXFET® is a registered trademark of Infineon.

\*Qualification standards can be found at [www.infineon.com](http://www.infineon.com)

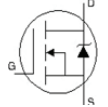
**Static @ T<sub>J</sub> = 25°C (unless otherwise specified)**

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	55	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.058	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	17.5	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 25A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	—	4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
g <sub>fs</sub>	Forward Trans conductance	19	—	—	S	V <sub>DS</sub> = 25V, I <sub>D</sub> = 25A ④
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	25	μA	V <sub>DS</sub> = 55V, V <sub>GS</sub> = 0V
		—	—	250	μA	V <sub>DS</sub> = 44V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 150°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-100	nA	V <sub>GS</sub> = -20V

**Dynamic Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)**

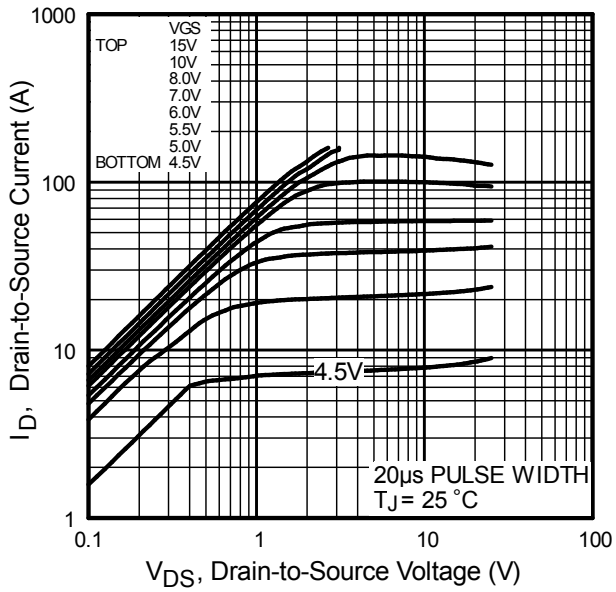
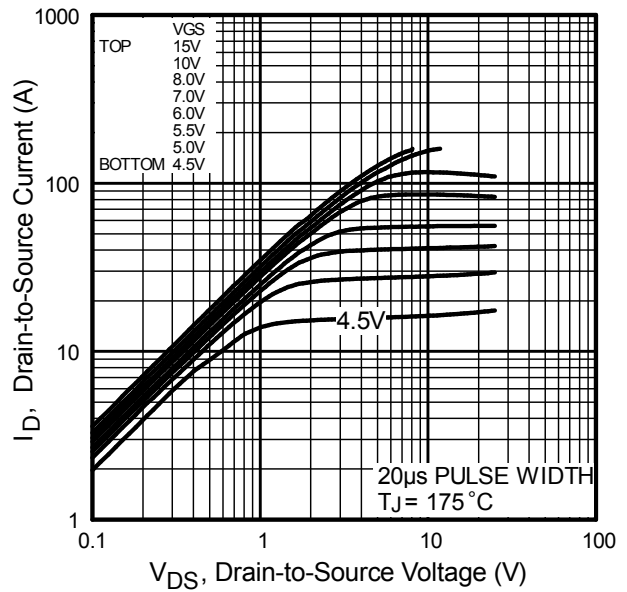
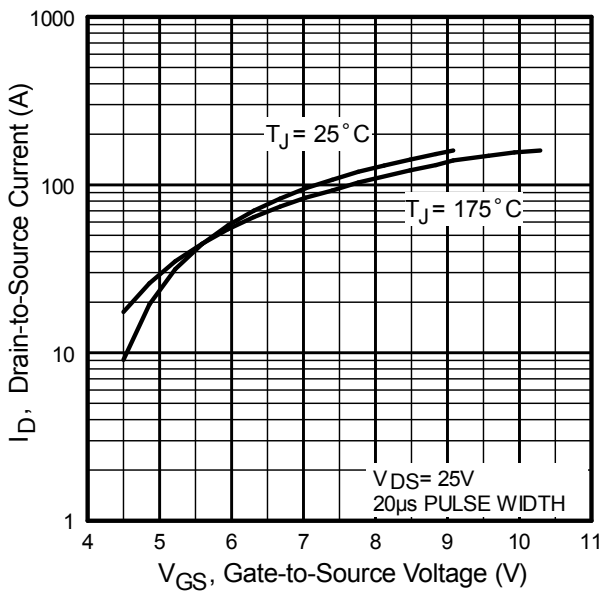
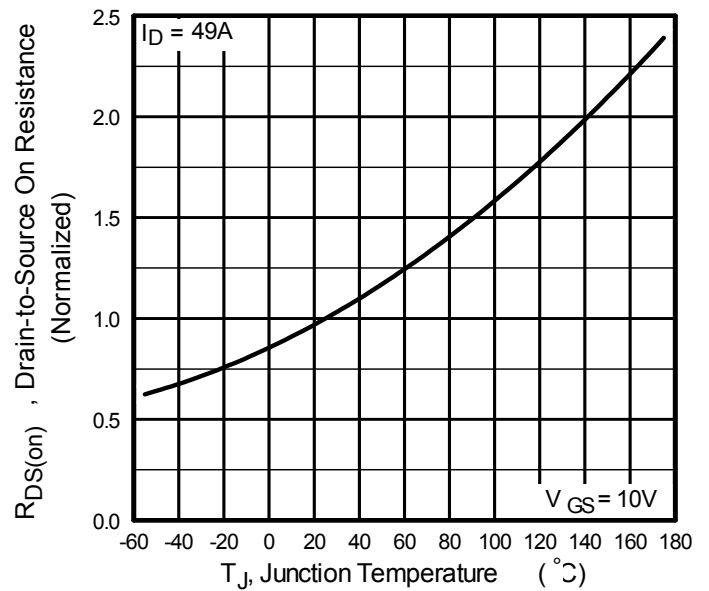
Q <sub>g</sub>	Total Gate Charge	—	—	63	nC	I <sub>D</sub> = 25A V <sub>DS</sub> = 44V V <sub>GS</sub> = 10V, See Fig. 6 and 13
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	14		
Q <sub>gd</sub>	Gate-to-Drain Charge	—	—	23		
t <sub>d(on)</sub>	Turn-On Delay Time	—	12	—	ns	V <sub>DD</sub> = 28V I <sub>D</sub> = 25A R <sub>G</sub> = 12Ω V <sub>GS</sub> = 10V, See Fig. 10 ④
t <sub>r</sub>	Rise Time	—	60	—		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	44	—		
t <sub>f</sub>	Fall Time	—	45	—		
L <sub>D</sub>	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact 
L <sub>S</sub>	Internal Source Inductance	—	7.5	—		
C <sub>iss</sub>	Input Capacitance	—	1470	—	pF	V <sub>GS</sub> = 0V V <sub>DS</sub> = 25V f = 1.0MHz, See Fig. 5
C <sub>oss</sub>	Output Capacitance	—	360	—		
C <sub>rss</sub>	Reverse Transfer Capacitance	—	88	—		
E <sub>As</sub>	Single pulse Avalanche Energy	—	530⑤	150⑥	mJ	I <sub>AS</sub> = 25A, L = 0.47mH

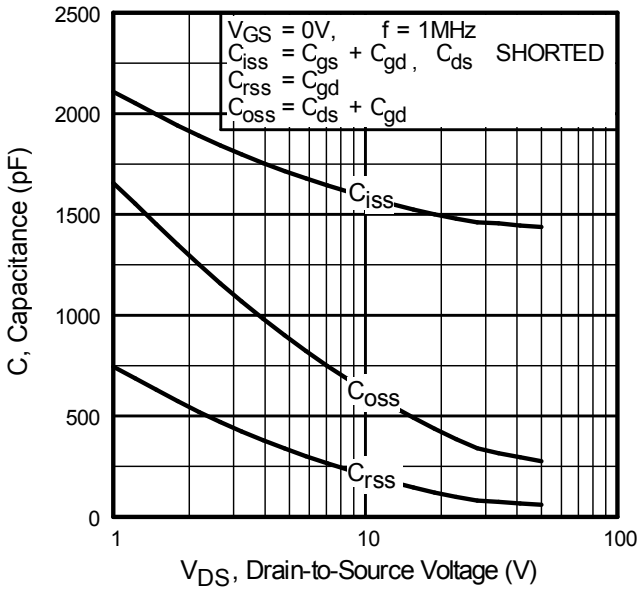
**Diode Characteristics**

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	49	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	160		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 25A, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	63	95	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 25A
Q <sub>rr</sub>	Reverse Recovery Charge	—	170	260	nC	di/dt = 100A/μs ④
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				

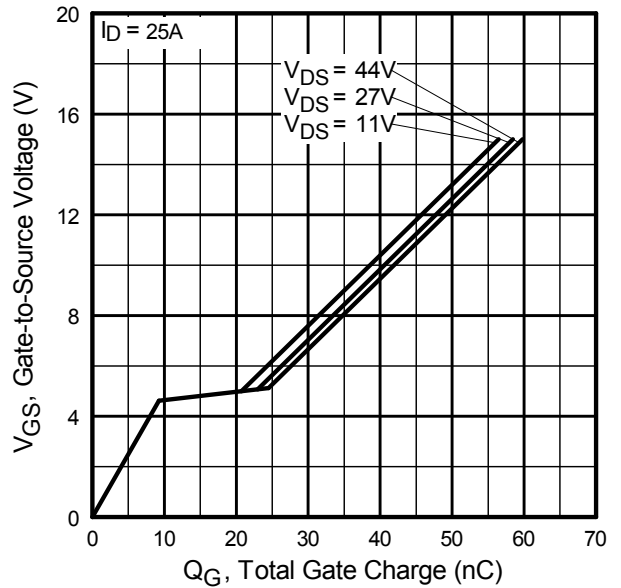
**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting T<sub>J</sub> = 25°C, L = 0.48mH, R<sub>G</sub> = 25Ω, I<sub>AS</sub> = 25A (See fig. 12)
- ③ I<sub>SD</sub> ≤ 25A, di/dt ≤ 230A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>J</sub> ≤ 175°C
- ④ Pulse width ≤ 400μs; duty cycle ≤ 2%.
- ⑤ This is a typical value at device destruction and represents operation outside rated limits.
- ⑥ This is a calculated value limited to T<sub>J</sub> = 175°C.

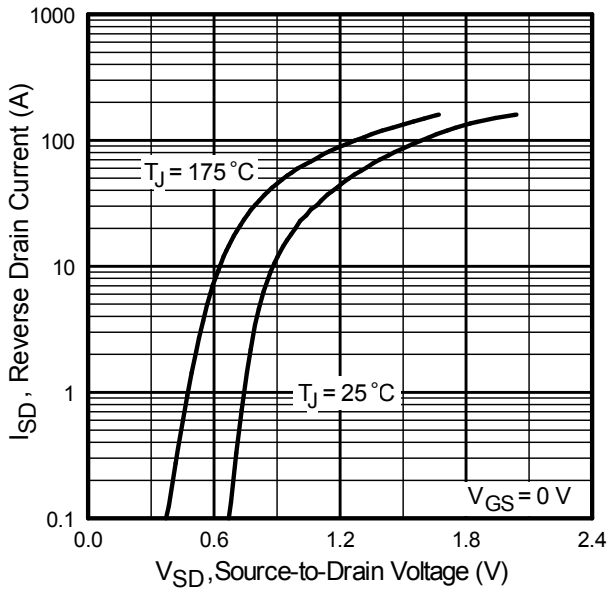

**Fig. 1** Typical Output Characteristics

**Fig. 2** Typical Output Characteristics

**Fig. 3** Typical Transfer Characteristics

**Fig. 4** Normalized On-Resistance Vs. Temperature



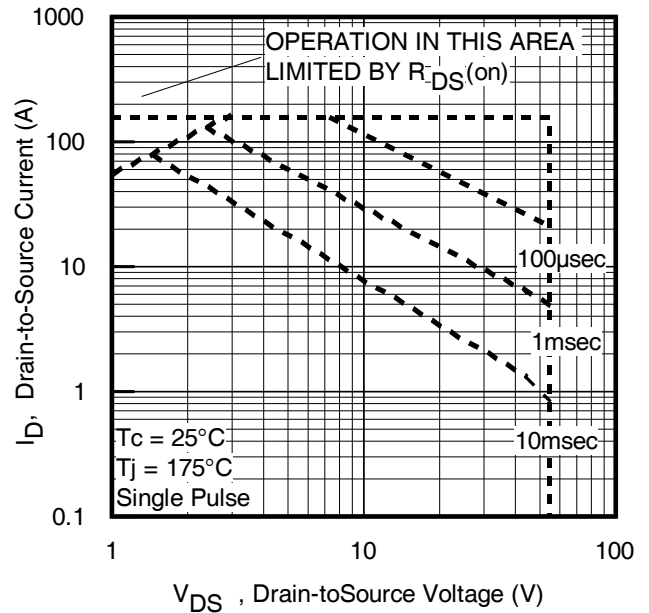
**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage



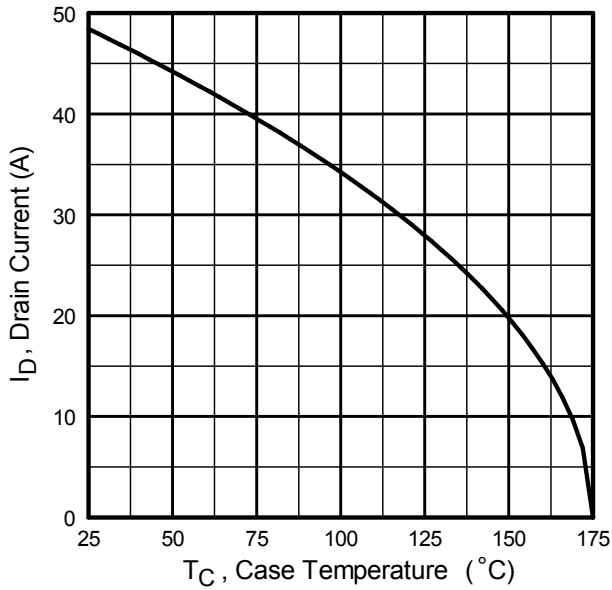
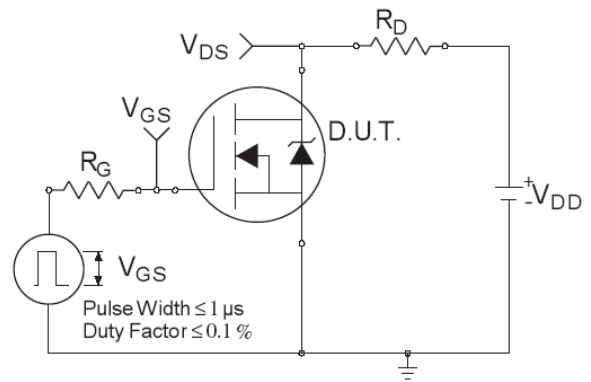
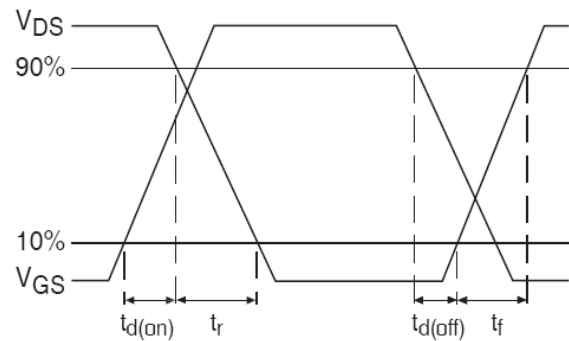
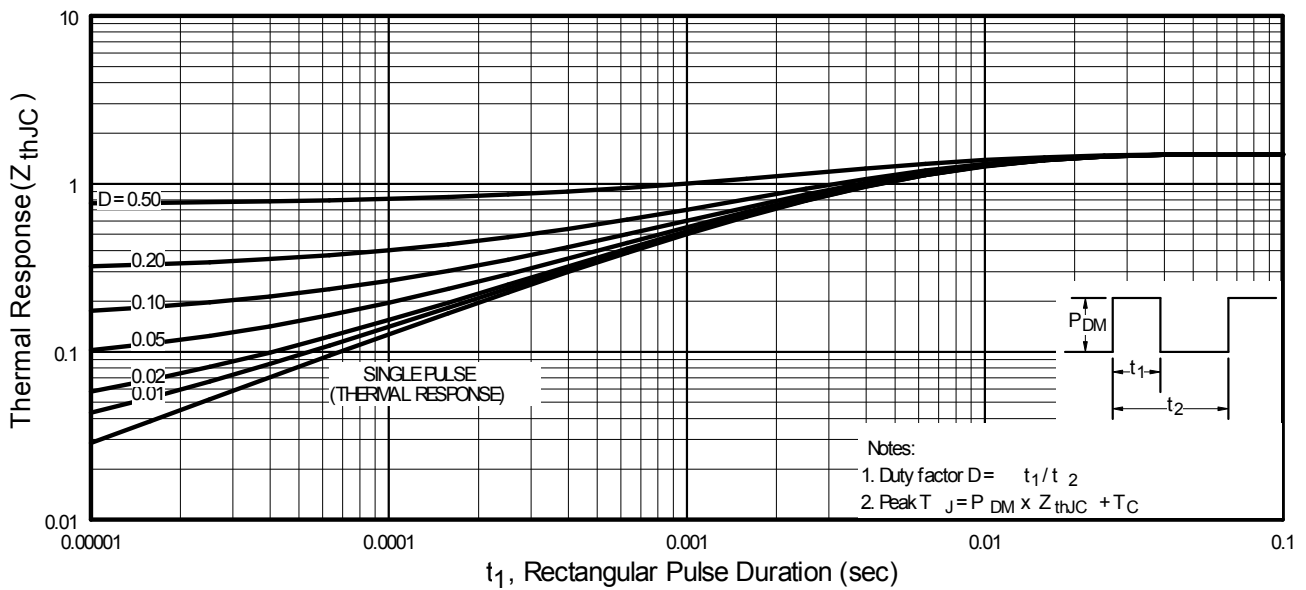
**Fig 6.** Typical Gate Charge vs. Gate-to-Source Voltage

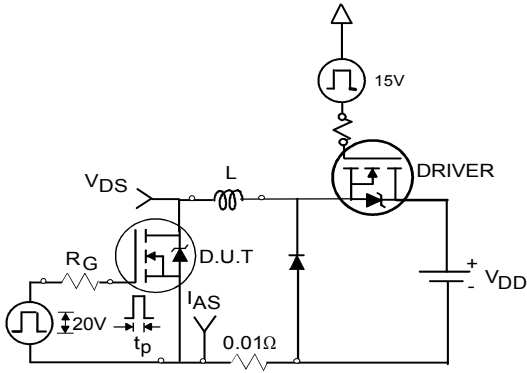
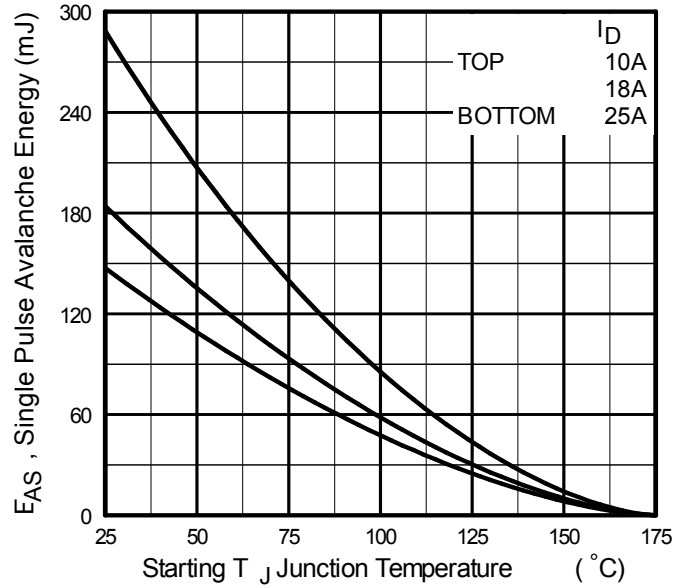
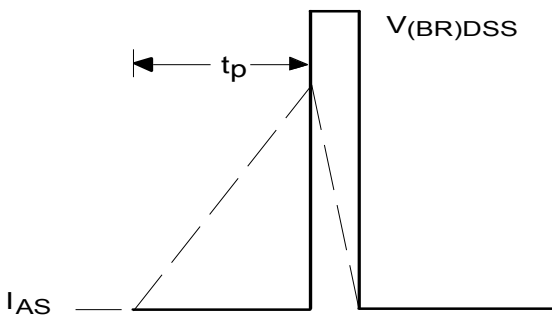
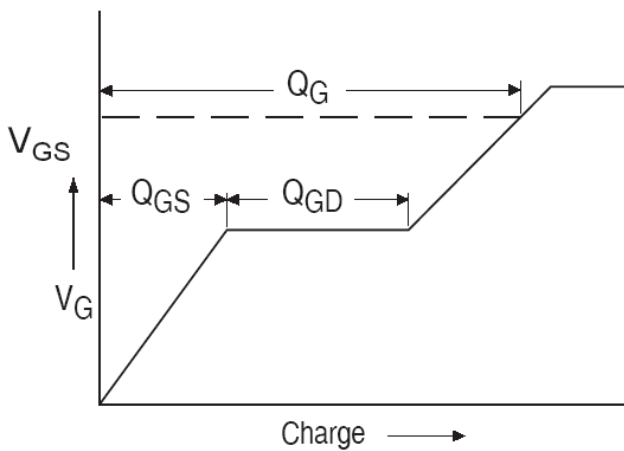
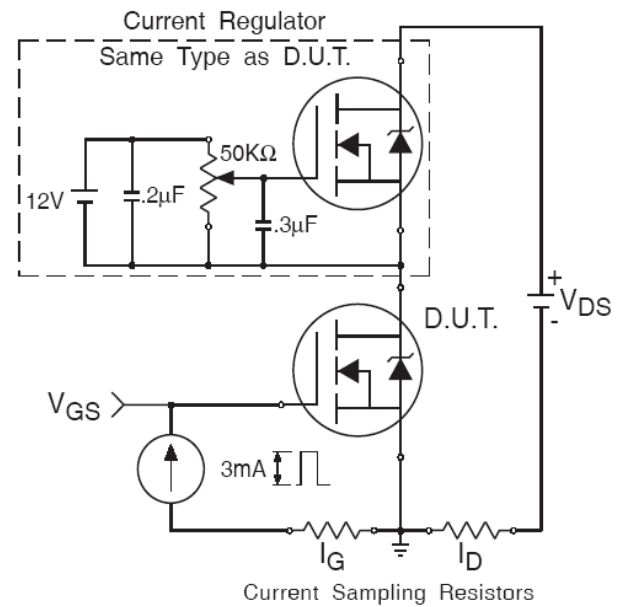


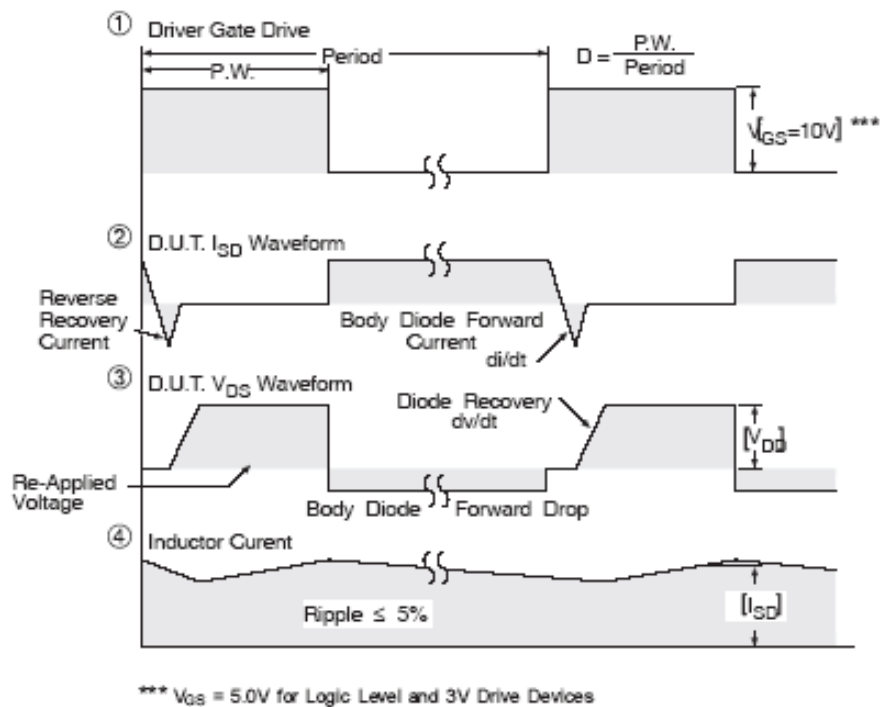
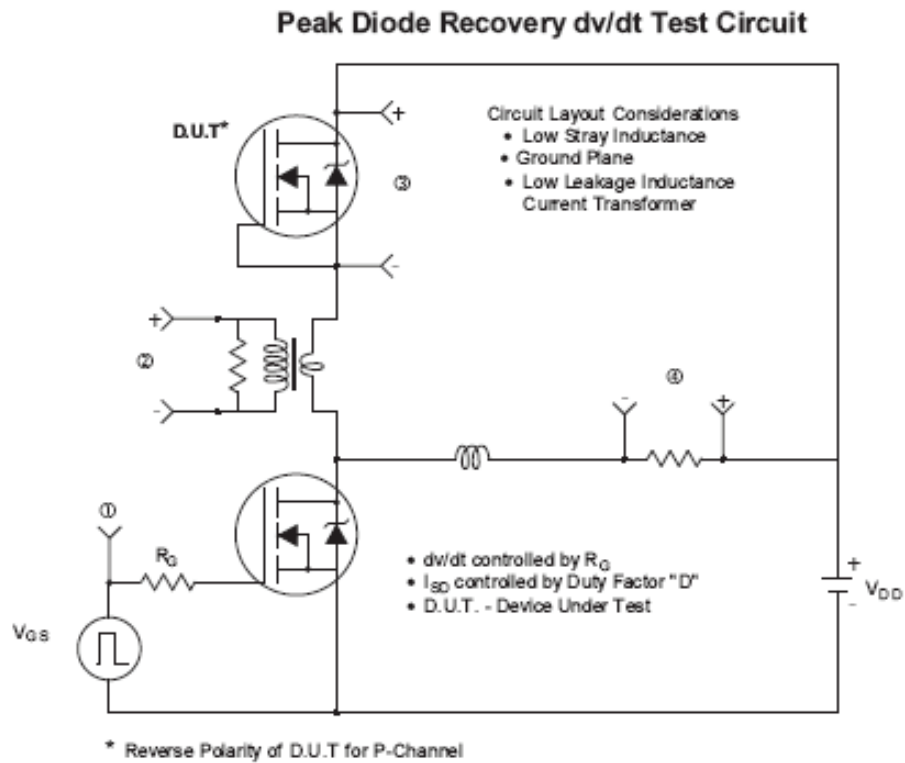
**Fig 7.** Typical Source-to-Drain Diode Forward Voltage

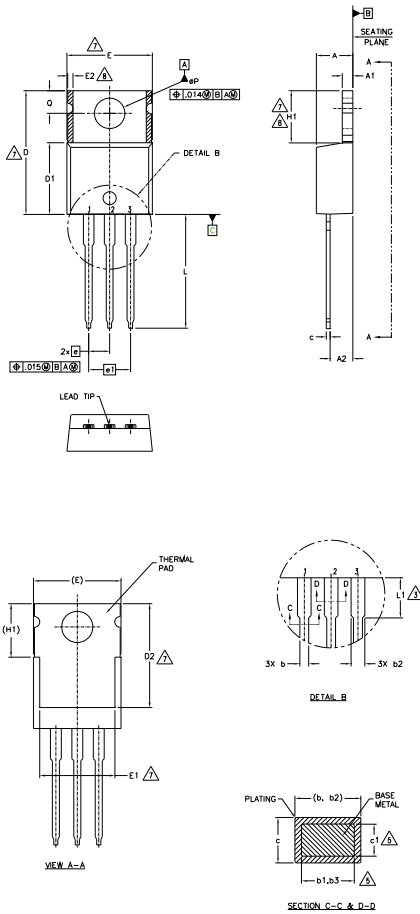


**Fig 8.** Maximum Safe Operating Area


**Fig 9.** Maximum Drain Current vs. Case Temperature

**Fig 10a.** Switching Time Test Circuit

**Fig 10b.** Switching Time Waveforms

**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case


**Fig 12a.** Unclamped Inductive Test Circuit

**Fig 12c.** Maximum Avalanche Energy vs. Drain Current

**Fig 12b.** Unclamped Inductive Waveforms

**Fig 13a.** Gate Charge Waveform

**Fig 13b.** Gate Charge Test Circuit


**Fig 14.** Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

**TO-220AB Package Outline (Dimensions are shown in millimeters (inches))**

**NOTES:**

- 1.- DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
- 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
- 3.- LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
- 4.- DIMENSION D, D1 & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 5.- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
- 6.- CONTROLLING DIMENSION : INCHES.
- 7.- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
- 8.- DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.
- 9.- OUTLINE CONFORMS TO JEDEC TO-220, EXCEPT A2 (max.) AND D2 (min.) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.83	.140	.190	
A1	1.14	1.40	.045	.055	
A2	2.03	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.97	.015	.038	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	11.68	12.88	.460	.507	7
E	9.65	10.67	.380	.420	4,7
E1	6.86	8.89	.270	.350	7
E2	-	0.76	-	.030	8
e	2.54 BSC		.100 BSC		
e1	5.08 BSC		.200 BSC		
H1	5.84	6.86	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	3.56	4.06	.140	.160	3
ØP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	

**LEAD ASSIGNMENTS**
**HEXFET**

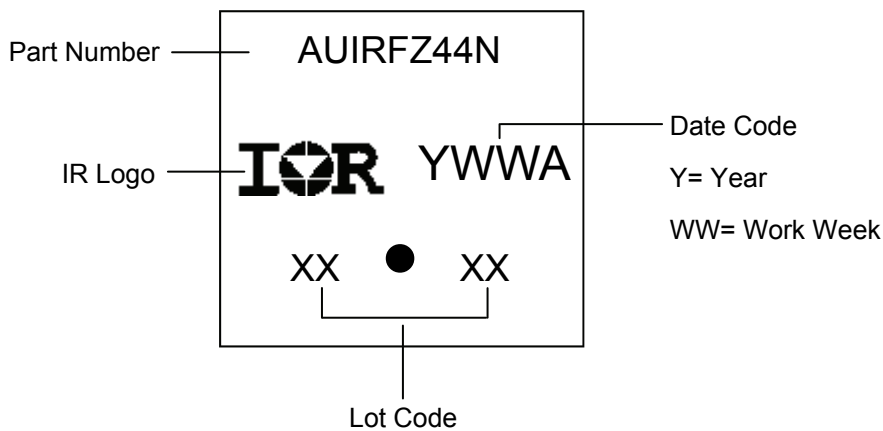
- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE

**IGBTs, CoPACK**

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER

**DIODES**

- 1.- ANODE
- 2.- CATHODE
- 3.- ANODE

**TO-220AB Part Marking Information**


TO-220AB package is not recommended for Surface Mount Application.



**Qualification Information**

<b>Qualification Level</b>		Automotive (per AEC-Q101)	
		Comments: This part number(s) passed Automotive qualification. Infineon's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
<b>Moisture Sensitivity Level</b>		3L-TO-220AB	N/A
<b>ESD</b>	Machine Model	Class M3 (+/- 400V) <sup>†</sup> AEC-Q101-002	
	Human Body Model	Class H1C (+/- 1250V) <sup>†</sup> AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 1250V) <sup>†</sup> AEC-Q101-005	
<b>RoHS Compliant</b>		Yes	

† Highest passing voltage.

**Revision History**

Date	Comments
9/25/2017	<ul style="list-style-type: none"> <li>Updated datasheet with corporate template.</li> <li>Corrected typo error on package outline and part marking on page 8.</li> </ul>

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